

# STGW40NC60KD

# 600 V, 40 A short-circuit rugged IGBT

Datasheet - production data

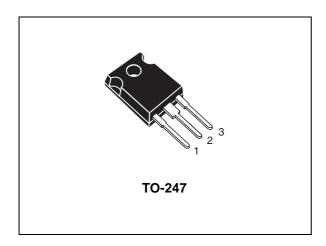
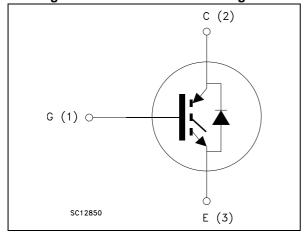


Figure 1. Internal schematic diagram



#### **Features**

- Low on-voltage drop (V<sub>CE(sat)</sub>)
- Low C<sub>res</sub> / C<sub>ies</sub> ratio (no cross conduction susceptibility)
- Short-circuit withstand time 10 μs
- IGBT co-packaged with ultra fast free-wheeling diode

## **Applications**

- · High frequency inverters
- Motor drivers

## **Description**

This IGBT utilizes the advanced PowerMESH™ process resulting in an excellent trade-off between switching performance and low on-state behavior.

**Table 1. Device summary** 

Order code	le Marking Package		Packaging
STGW40NC60KD	GW40NC60KD	TO-247	Tube

Contents STGW40NC60KD

## **Contents**

1	Electrical ratings 3
2	Electrical characteristics4
	2.1 Electrical characteristics (curves)
3	Test circuits9
4	Package mechanical data10
5	Revision history12

STGW40NC60KD Electrical ratings

# 1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V <sub>CES</sub>	Collector-emitter voltage (V <sub>GE</sub> = 0)	600	V
I <sub>C</sub> <sup>(1)</sup>	Collector current (continuous) at T <sub>C</sub> = 25 °C	70	Α
I <sub>C</sub> <sup>(1)</sup>	Collector current (continuous) at T <sub>C</sub> = 100 °C	38	Α
I <sub>CL</sub> <sup>(2)</sup>	Turn-off latching current 220		Α
I <sub>CP</sub> <sup>(3)</sup>	Pulsed collector current	220	Α
$V_{GE}$	Gate-emitter voltage ±20		V
I <sub>F</sub>	Diode RMS forward current at T <sub>C</sub> = 25 °C 30		Α
I <sub>FSM</sub>	Surge non repetitive forward current $t_p = 10 \text{ ms}$ sinusoidal	120	Α
P <sub>TOT</sub>	Total dissipation at T <sub>C</sub> = 25 °C	250	W
t <sub>scw</sub>	Short circuit withstand time, $V_{CE} = 0.5 V_{(BR)CES}$ $T_j = 125^{\circ}C$ , $R_G = 10 \Omega$ , $V_{GE} = 12 V$	10	μs
T <sub>j</sub>	Operating junction temperature	- 55 to 150	°C

1. Calculated according to the iterative formula:

$$I_{c}(T_{c}) = \frac{T_{J(MAX)} - T_{c}}{R_{thj-c} \times V_{CE(sat)(MAX)} \cdot (T_{c}, I_{c})}$$

- 2.  $V_{clamp} = 80\%, (V_{CES}), T_j = 150$ °C,  $R_G = 10 \Omega, V_{GE} = 15 V$
- 3. Pulse width limited by max. junction temperature allowed

Table 3. Thermal resistance

Symbol	Parameter	Value	Unit
D	Thermal resistance junction-case IGBT max.	0.5	°C/W
R <sub>thj-case</sub> Thermal resistance junction-case diode max.		1.5	°C/W
R <sub>thj-amb</sub>	Thermal resistance junction-ambient max	50	°C/W

Electrical characteristics STGW40NC60KD

# 2 Electrical characteristics

T<sub>CASE</sub>=25°C unless otherwise specified.

Table 4. Static

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
V <sub>(BR)CES</sub>	Collector-emitter breakdown voltage (V <sub>GE</sub> = 0)	I <sub>C</sub> = 1 mA	600			V
V <sub>CE(sat)</sub>	Collector-emitter saturation voltage	$V_{GE} = 15 \text{ V}, I_{C} = 30 \text{ A}$ $V_{GE} = 15 \text{ V}, I_{C} = 30 \text{ A},$ $T_{C} = 125 \text{ °C}$		2.1	2.7	V V
I <sub>CES</sub>	Collector cut-off current (V <sub>GE</sub> = 0)	V <sub>CE</sub> = 600 V V <sub>CE</sub> = 600 V, T <sub>C</sub> = 125 °C			500 5	μA mA
V <sub>GE(th)</sub>	Gate threshold voltage	$V_{CE} = V_{GE}, I_{C} = 250 \mu A$	4.5		6.5	V
I <sub>GES</sub>	Gate-emitter cut-off current (V <sub>CE</sub> = 0)	V <sub>GE</sub> = ±20 V			±100	nA
9 <sub>fs</sub> <sup>(1)</sup>	Forward transconductance	V <sub>CE</sub> = 15 V <sub>,</sub> I <sub>C</sub> = 30 A		20		S

<sup>1.</sup> Pulsed: Pulse duration = 300 μs, duty cycle 1.5%

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
C <sub>ies</sub> C <sub>oes</sub> C <sub>res</sub>	Input capacitance Output capacitance Reverse transfer capacitance	$V_{CE} = 25 \text{ V, f} = 1 \text{ MHz, V}_{GE} = 0$	-	2870 295 69		pF pF pF
Q <sub>g</sub> Q <sub>ge</sub> Q <sub>gc</sub>	Total gate charge Gate-emitter charge Gate-collector charge	$V_{CE} = 480 \text{ V}, I_{C} = 30 \text{ A},$ $V_{GE} = 15 \text{ V}$ (see Figure 18)	-	135 27 69.5	-	nC nC nC

Table 6. Switching on/off (inductive load)

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
t <sub>d(on)</sub> t <sub>r</sub> (di/dt) <sub>on</sub>	Turn-on delay time Current rise time Turn-on current slope	$V_{CC}$ = 480 V, $I_{C}$ = 30 A $R_{G}$ =10 $\Omega$ , $V_{GE}$ = 15 V, (see Figure 17)	-	46 18.5 1530	-	ns ns A/µs
t <sub>d(on)</sub> t <sub>r</sub> (di/dt) <sub>on</sub>	Turn-on delay time Current rise time Turn-on current slope	$V_{CC} = 480 \text{ V}, I_{C} = 30 \text{ A}$ $R_{G} = 10 \Omega, V_{GE} = 15 \text{ V},$ $T_{C} = 125 ^{\circ}\text{C} \text{ (see Figure 17)}$	-	45 19 1400	-	ns ns A/µs
t <sub>r(Voff)</sub> t <sub>d(off)</sub> t <sub>f</sub>	Off voltage rise time Turn-off delay time Current fall time	$V_{CC}$ = 480 V, $I_{C}$ = 30 A $R_{G}$ =10 $\Omega$ , $V_{GE}$ = 15 V, (see Figure 17)	-	38 164 87	-	ns ns ns
$t_{r(Voff)} \\ t_{d(off)} \\ t_{f}$	Off voltage rise time Turn-off delay time Current fall time	$V_{cc} = 480 \text{ V}, I_{C} = 30 \text{ A},$ $R_{G} = 10 \Omega, V_{GE} = 15 \text{ V}$ $T_{C} = 125 \text{ °C}$ (see Figure 17)	-	70 208 130	-	ns ns ns

Table 7. Switching energy (inductive load)

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
E <sub>on</sub> E <sub>off</sub> <sup>(1)</sup> E <sub>ts</sub>	Turn-on switching losses Turn-off switching losses Total switching losses	$V_{CC}$ = 480 V, $I_{C}$ = 30 A $R_{G}$ = 10 $\Omega$ , $V_{GE}$ = 15 V, (see Figure 17)	-	595 716 1311	-	μJ μJ μJ
E <sub>on</sub> E <sub>off</sub> <sup>(1)</sup> E <sub>ts</sub>	Turn-on switching losses Turn-off switching losses Total switching losses	$V_{CC} = 480 \text{ V}, I_{C} = 30 \text{ A}$ $R_{G} = 10 \Omega, V_{GE} = 15 \text{ V},$ $T_{C} = 125 ^{\circ}\text{C}$ (see Figure 17)	-	808 1200 2008	-	µJ µJ µJ

<sup>1.</sup> Turn-off losses include also the tail of the collector current.

Table 8. Collector-emitter diode

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
V <sub>F</sub>	Forward on-voltage	I <sub>F</sub> = 30 A I <sub>F</sub> = 30 A, T <sub>C</sub> = 125 °C	-	2.4 1.8	-	V V
t <sub>rr</sub> Q <sub>rr</sub> I <sub>rrm</sub>	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_F = 30 \text{ A}, V_R = 50 \text{ V},$ di/dt = 100 A/ $\mu$ s (see Figure 20)	-	45 56 2.55	-	ns nC A
t <sub>rr</sub> Q <sub>rr</sub> I <sub>rrm</sub>	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_F = 30 \text{ A}, V_R = 50 \text{ V},$ $T_C = 125 ^{\circ}\text{C},  \text{di/dt} = 100$ $A/\mu s$ (see Figure 20)	-	100 290 5.8	-	ns nC A

Electrical characteristics STGW40NC60KD

## 2.1 Electrical characteristics (curves)

Figure 2. Output characteristics

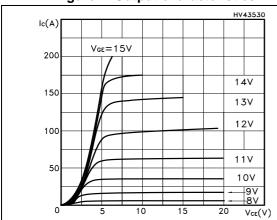


Figure 3. Transfer characteristics

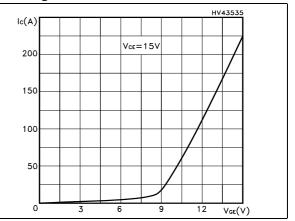
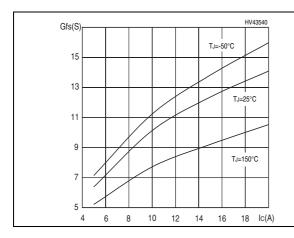


Figure 4. Transconductance

Figure 5. Collector-emitter on voltage vs. temperature



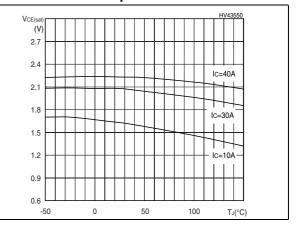


Figure 6. Gate charge vs. gate-source voltage

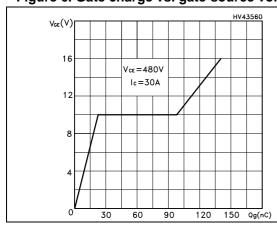


Figure 7. Capacitance variations

HV43570

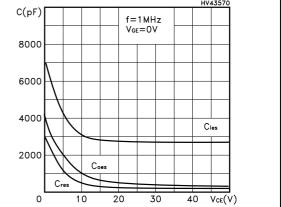
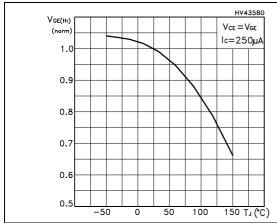


Figure 8. Normalized gate threshold voltage vs. temperature

Figure 9. Collector-emitter on voltage vs. collector current



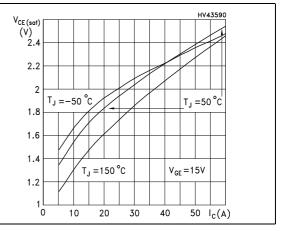
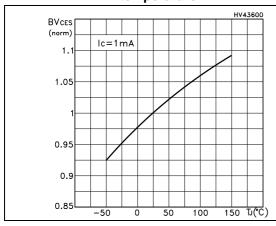


Figure 10. Normalized breakdown voltage vs. temperature

Figure 11. Switching losses vs. temperature



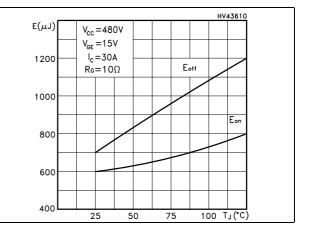
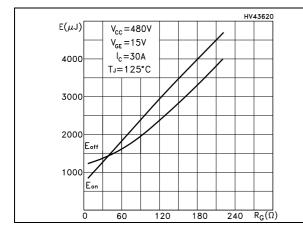
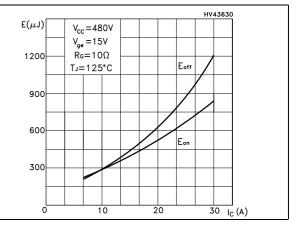


Figure 12. Switching losses vs. gate resistance

Figure 13. Switching losses vs. collector current





Electrical characteristics STGW40NC60KD

Figure 14. Thermal Impedance

K  $\delta c c 20530$   $\delta = 0.5$  0.2  $Z_{th} = k R_{thJ-c}$   $\delta = t_p/\tau$ 

Figure 15. Turn-off SOA

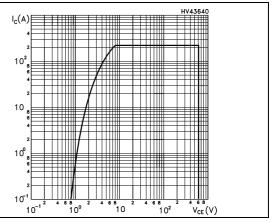


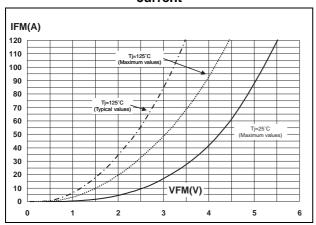
Figure 16. Forward voltage drop vs. forward current

10 -3

 $10^{-2}$ 

 $10^{-1} t_p(s)$ 

10-4



STGW40NC60KD Test circuits

## 3 Test circuits

Figure 17. Test circuit for inductive load switching

Figure 18. Gate charge test circuit

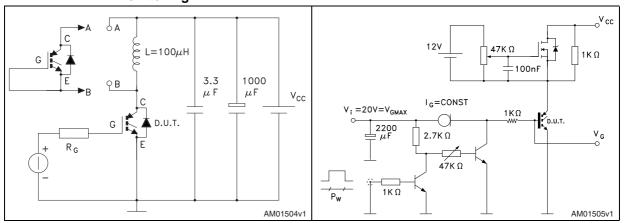
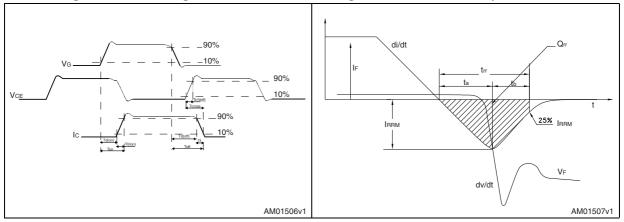


Figure 19. Switching waveform

Figure 20. Diode recovery time waveform



# 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: <a href="https://www.st.com">www.st.com</a>. ECOPACK<sup>®</sup> is an ST trademark.

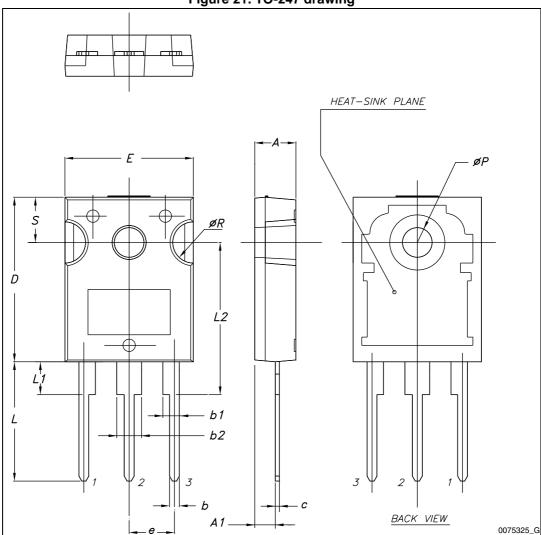


Figure 21. TO-247 drawing

Table 9. TO-247 mechanical data

Dim		mm.	
Dim.	Min.	Тур.	Max.
А	4.85		5.15
A1	2.20		2.60
b	1.0		1.40
b1	2.0		2.40
b2	3.0		3.40
С	0.40		0.80
D	19.85		20.15
E	15.45		15.75
е	5.30	5.45	5.60
L	14.20		14.80
L1	3.70		4.30
L2		18.50	
ØP	3.55		3.65
ØR	4.50		5.50
S	5.30	5.50	5.70



Revision history STGW40NC60KD

# 5 Revision history

Table 10. Document revision history

Date	Revision	Changes
11-Jun-2008	1	Initial release
12-Mar-2014	2	Modified total switching losses typical value in <i>Table 7:</i> Switching energy (inductive load). Minor text changes.

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